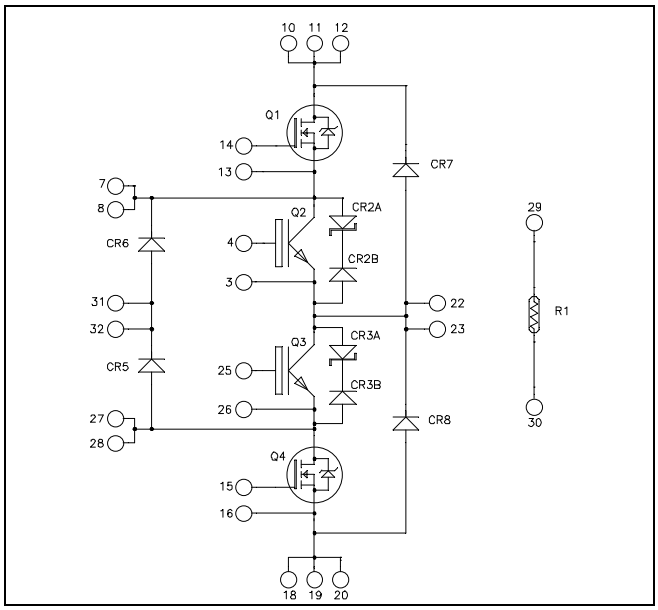
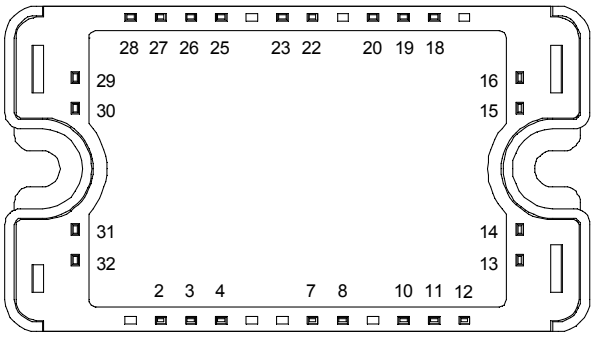
APTCV60TLM45T3G

Three level inverter
CoolMOS & Trench + Field Stop IGBT3
Power Module

Trench & Field Stop IGBT3 Q2, Q3:
V_{CES} = 600V ; I_C = 75A @ Tc = 80°C

CoolMOS™ Q1, Q4:
V_{DSS} = 600V ; I_D = 38A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 10/11/12 ; 7/8 …

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- ***Q2, Q3 Trench + Field Stop IGBT3 Technology***
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- ***Q1, Q4 CoolMOS™***
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
See application note APT0502 on www.microsemi.com

Q1 & Q4 Absolute maximum ratings (per CoolMOS™)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage		600	V
I_D	Continuous Drain Current	T_c = 25°C	49	A
		T_c = 80°C	38	
I_{DM}	Pulsed Drain current		130	
V_{GS}	Gate - Source Voltage		±20	V
R_{DSon}	Drain - Source ON Resistance		45	mΩ
P_D	Maximum Power Dissipation	T_c = 25°C	250	W
I_{AR}	Avalanche current (repetitive and non repetitive)		15	A
E_{AR}	Repetitive Avalanche Energy		3	mJ
E_{AS}	Single Pulse Avalanche Energy		1900	

Q1 & Q4 Electrical Characteristics (per CoolMOS™)

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 600V	T_j = 25°C			250	µA
		V_{GS} = 0V, V_{DS} = 600V	T_j = 125°C			500	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 24.5A			40	45	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 3mA		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				100	nA

Q1 & Q4 Dynamic Characteristics (per CoolMOS™)

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V ; V_{DS} = 25V f = 1MHz		7.2		nF
C_{oss}	Output Capacitance			8.5		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 300V I_D = 49A		150		nC
Q_{gs}	Gate – Source Charge			34		
Q_{gd}	Gate – Drain Charge			51		
$T_{d(on)}$	Turn-on Delay Time	**Inductive Switching (125°C)** V_{GS} = 10V V_{Bus} = 400V I_D = 49A R_G = 5Ω		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			100		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 10V ; V_{Bus} = 400V I_D = 49A ; R_G = 5Ω		675		µJ
E_{off}	Turn-off Switching Energy			520		
E_{on}	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 10V ; V_{Bus} = 400V I_D = 49A ; R_G = 5Ω		1100		µJ
E_{off}	Turn-off Switching Energy			635		
R_{thJC}	Junction to Case Thermal Resistance				0.5	°C/W

Q2 & Q3 Absolute maximum ratings (per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	100	A
		T_C = 80°C	75	
I_{CM}	Pulsed Collector Current	T_C = 25°C	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	250	W
RBSOA	Reverse Bias Safe Operating Area	T_J = 150°C	150A @ 550V	

Q2 & Q3 Electrical Characteristics (per IGBT)

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V				250	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V, I_C = 75A	T_j = 25°C		1.5	1.9	V
			T_j = 150°C		1.7		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 600µA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Q2 & Q3 Dynamic Characteristics (per IGBT)

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			4620		pF
C_{oes}	Output Capacitance				300		
C_{res}	Reverse Transfer Capacitance				140		
Q_G	Gate charge	V_{GE}=±15V, I_C=75A V_{CE}=300V			0.8		µC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω			110		ns
T_r	Rise Time				45		
$T_{d(off)}$	Turn-off Delay Time				200		
T_f	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω			120		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				250		
T_f	Fall Time				60		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω	T_j = 25°C		0.35		mJ
			T_j = 150°C		0.6		
E_{off}	Turn-off Switching Energy		T_j = 25°C		2.2		mJ
			T_j = 150°C		2.6		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 360V t_p ≤ 6µs ; T_j = 150°C			380		A
R_{thJC}	Junction to Case Thermal Resistance					0.60	°C/W

CR2 & CR3 diode ratings and characteristics (per device)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_F	Diode + tranzorb Forward Voltage	I_F = 10A			10		V
R_{thJC}	Junction to Case Thermal Resistance					8	°C/W

CR5 & CR6 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	V_R=600V				25	µA
I_F	DC Forward Current		Tc = 80°C		30		A
V_F	Diode Forward Voltage	I_F = 30A			1.8	2.2	V
		I_F = 60A			2.2		
		I_F = 30A	T_j = 125°C		1.5		
t_{rr}	Reverse Recovery Time	I_F = 30A V_R = 400V di/dt =200A/µs	T_j = 25°C		25		ns
			T_j = 125°C		160		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		35		nC
			T_j = 125°C		480		
E_{rr}	Reverse Recovery Energy	I_F = 30A V_R = 400V di/dt =1000A/µs	T_j = 125°C		0.6		mJ
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

CR7 & CR8 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V				100	µA
I_F	DC Forward Current		Tc = 80°C		30		A
V_F	Diode Forward Voltage	I_F = 30A			2.6	3.1	V
		I_F = 60A			3.2		
		I_F = 30A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 30A V_R = 800V di/dt =200A/µs	T_j = 25°C		300		ns
			T_j = 125°C		380		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		360		nC
			T_j = 125°C		1700		
E_{rr}	Reverse Recovery Energy	I_F = 30A V_R = 800V di/dt =1000A/µs	T_j = 125°C		1.6		mJ
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
ΔB/B		T_C=100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

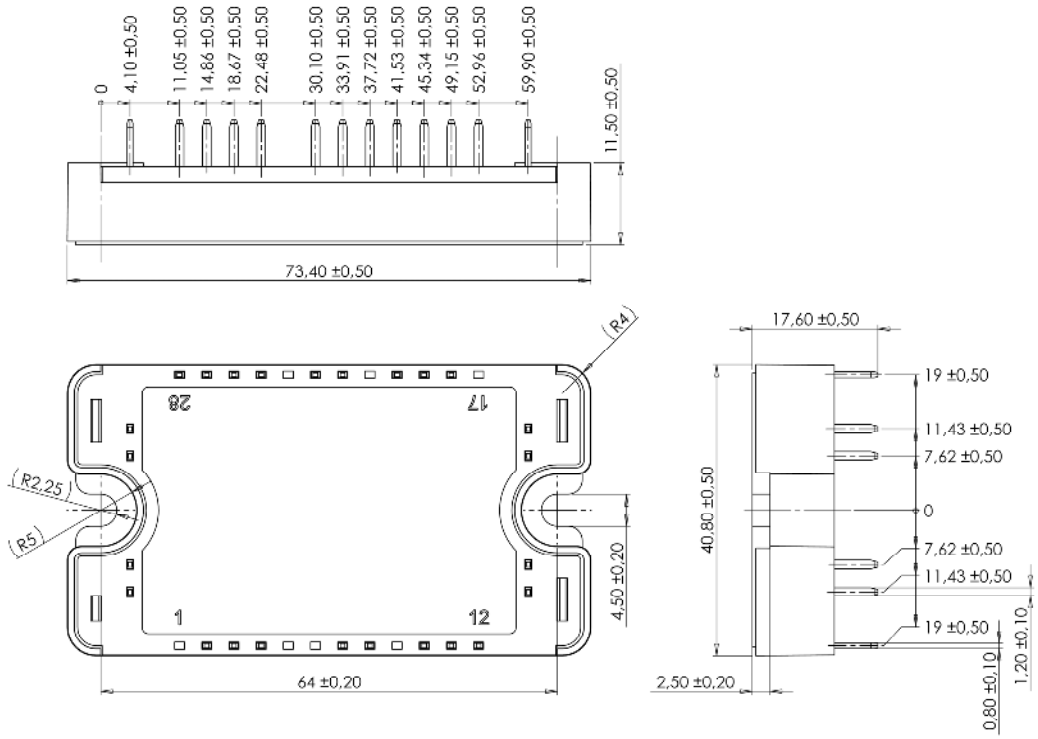
T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	*Characteristic*			*Min*	*Typ*	*Max*	*Unit*
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		175*	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

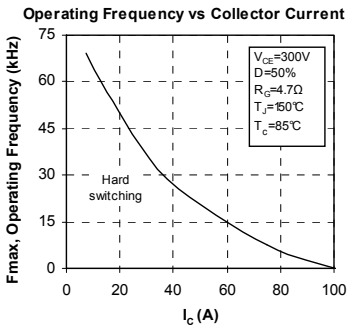
* Tjmax = 150°C for Q1 & Q4

SP3 Package outline (dimensions in mm)

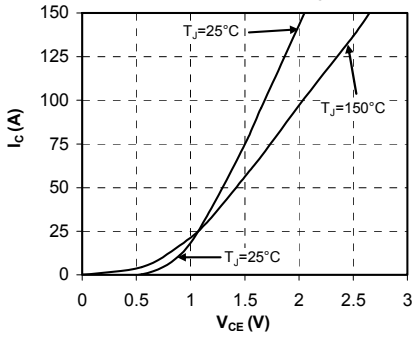


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

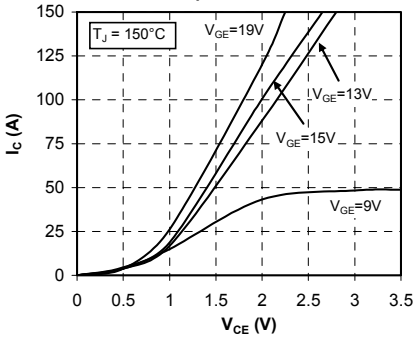
Q2 & Q3 Typical performance curve



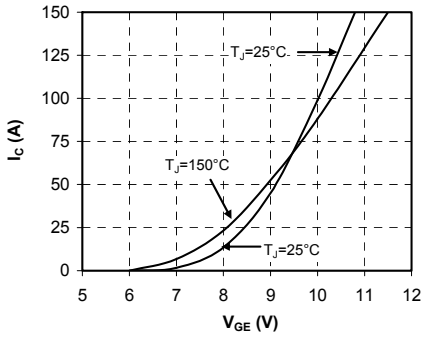
Output Characteristics (V_{GE}=15V)



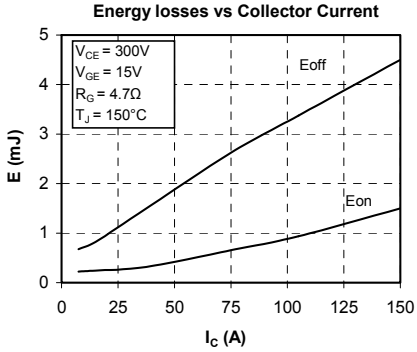
Output Characteristics



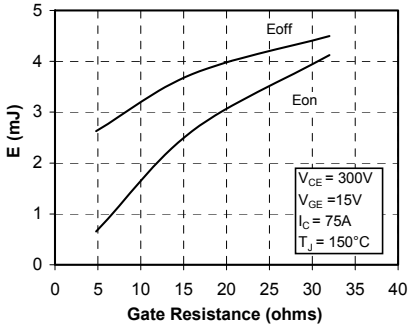
Transfert Characteristics



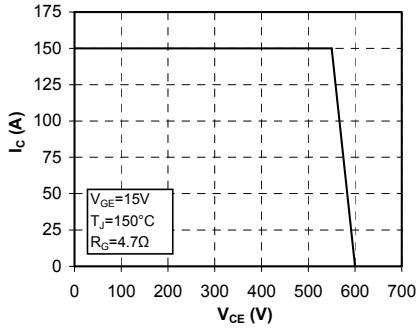
Energy losses vs Collector Current



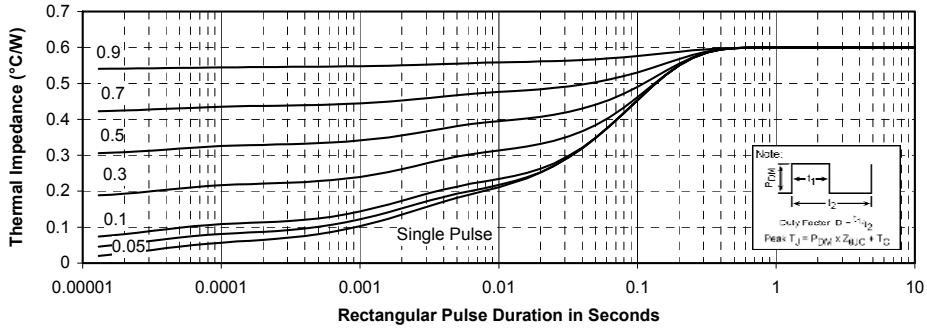
Switching Energy Losses vs Gate Resistance



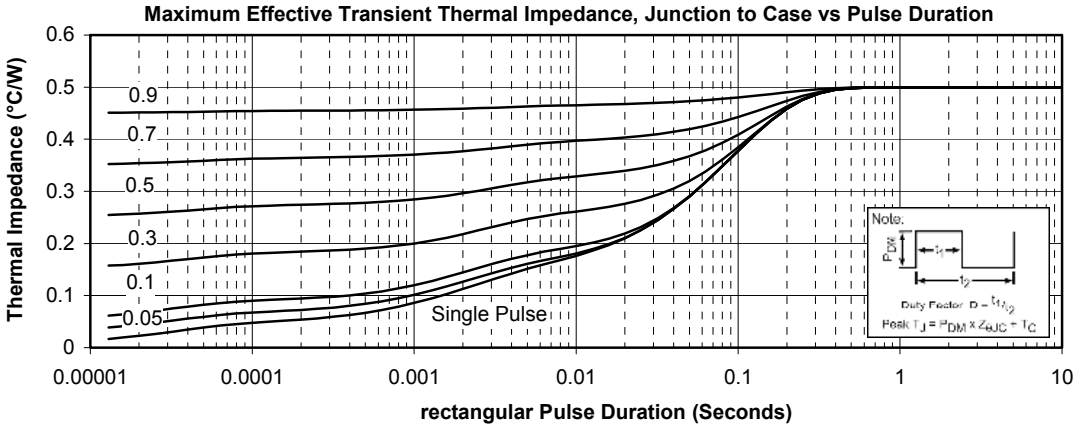
Reverse Bias Safe Operating Area

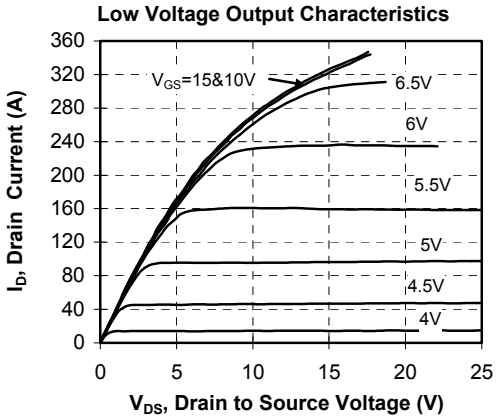


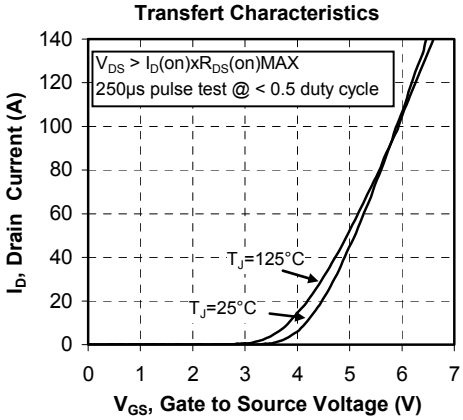
maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

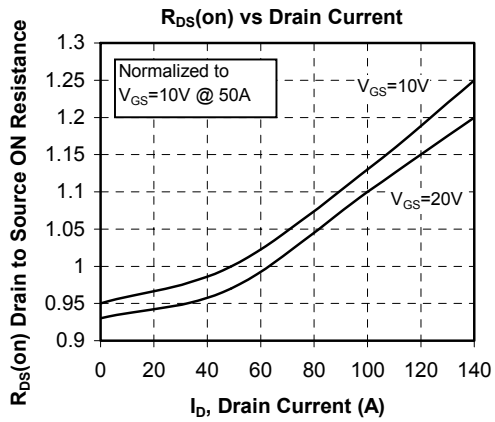


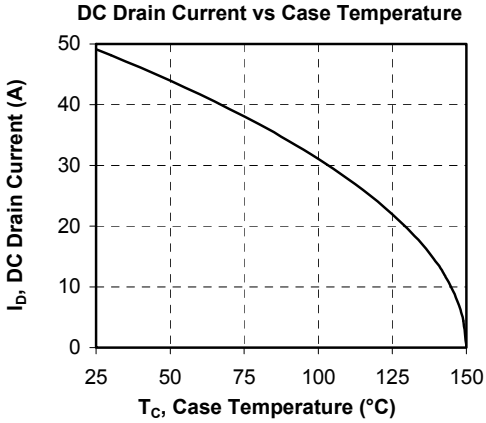
Q1 & Q4 Typical performance curve



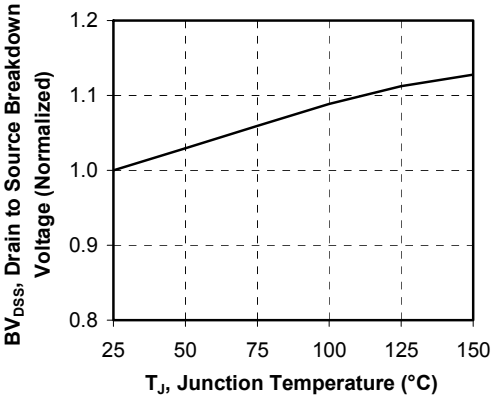




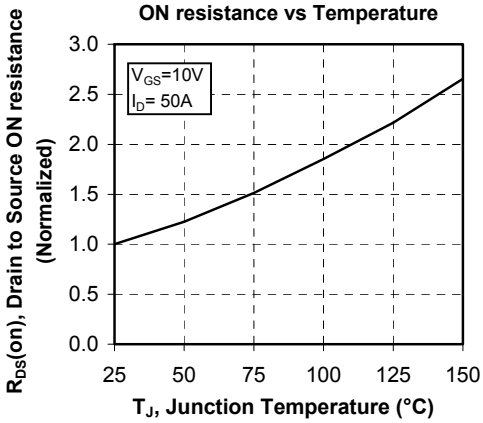




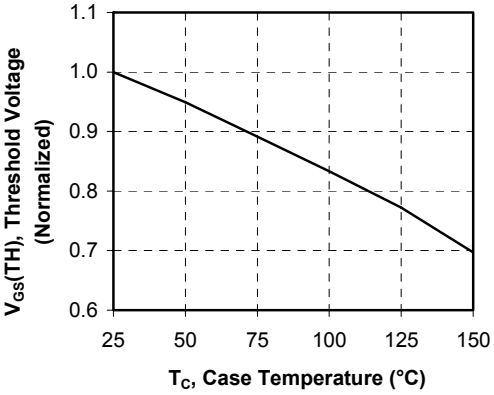
Breakdown Voltage vs Temperature



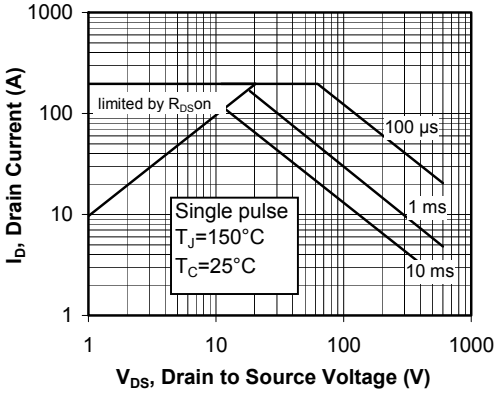
ON resistance vs Temperature



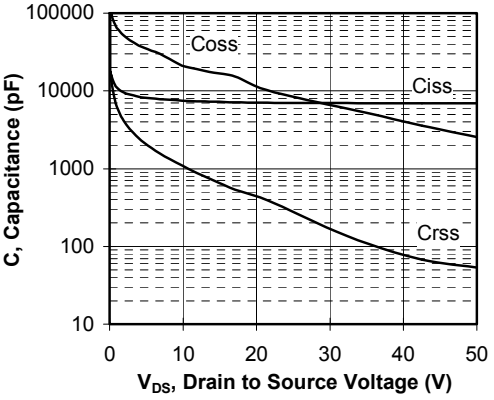
Threshold Voltage vs Temperature



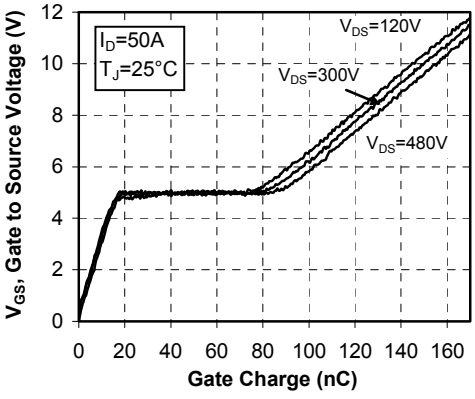
Maximum Safe Operating Area



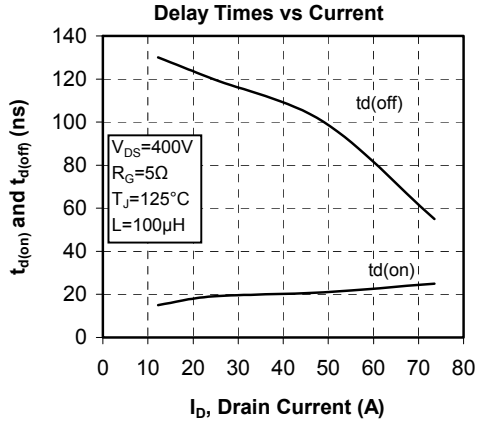
Capacitance vs Drain to Source Voltage



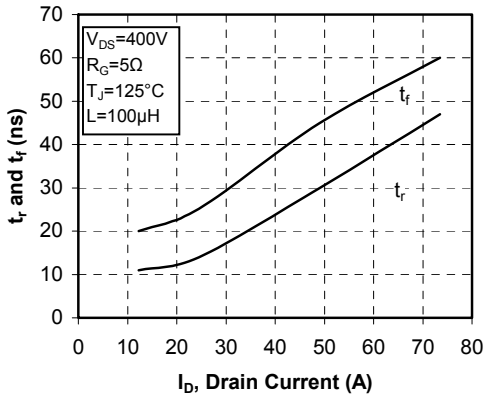
Gate Charge vs Gate to Source Voltage



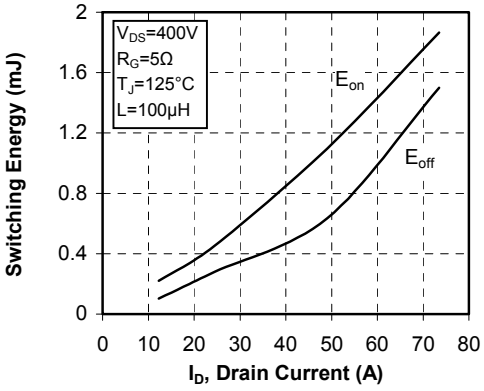
Delay Times vs Current



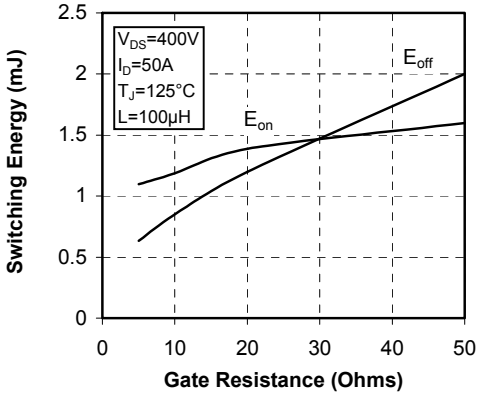
Rise and Fall times vs Current



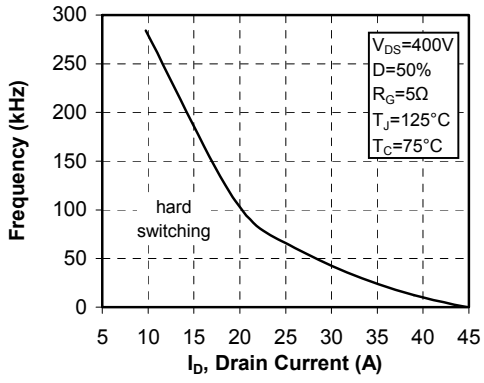
Switching Energy vs Current



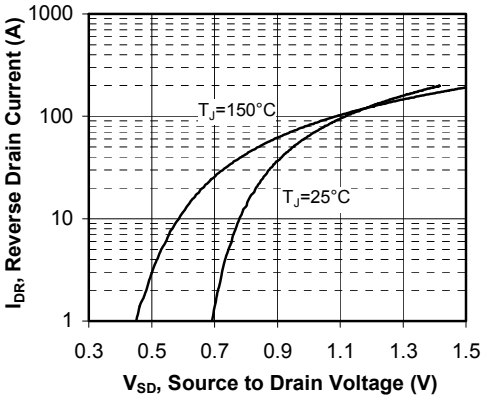
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current

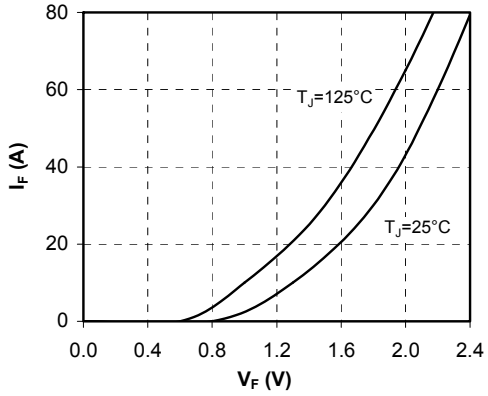


Source to Drain Diode Forward Voltage

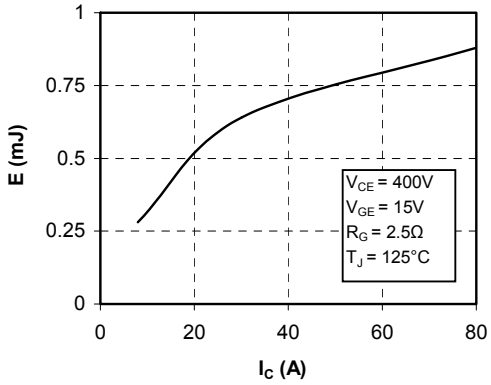


CR5 & CR6 Typical performance curve

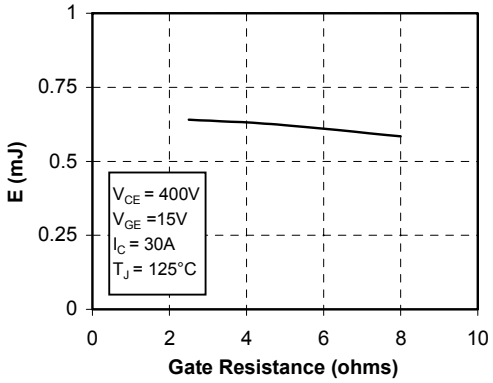
Forward Characteristic of diode



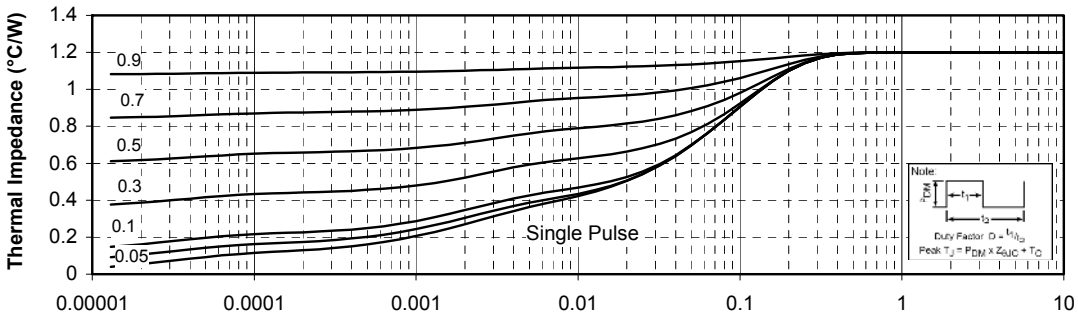
Energy losses vs Collector Current



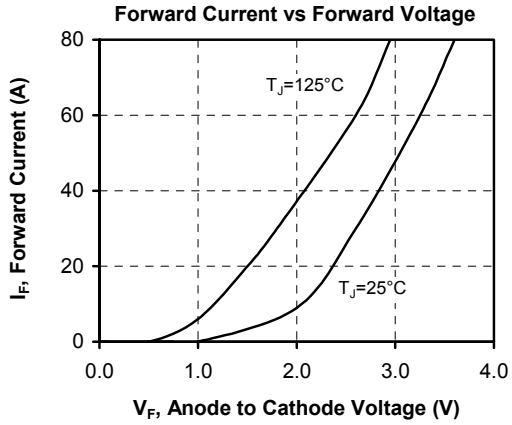
Switching Energy Losses vs Gate Resistance

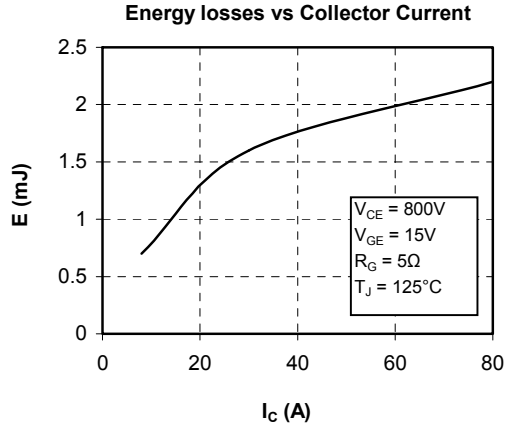


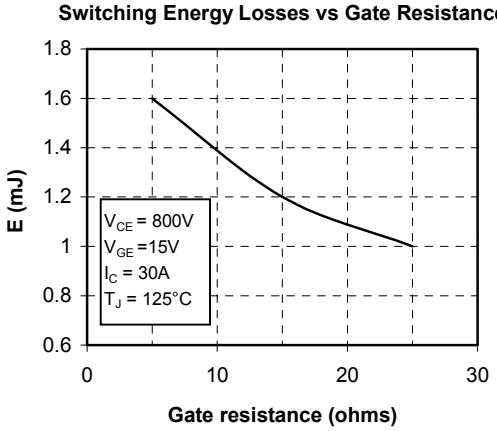
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

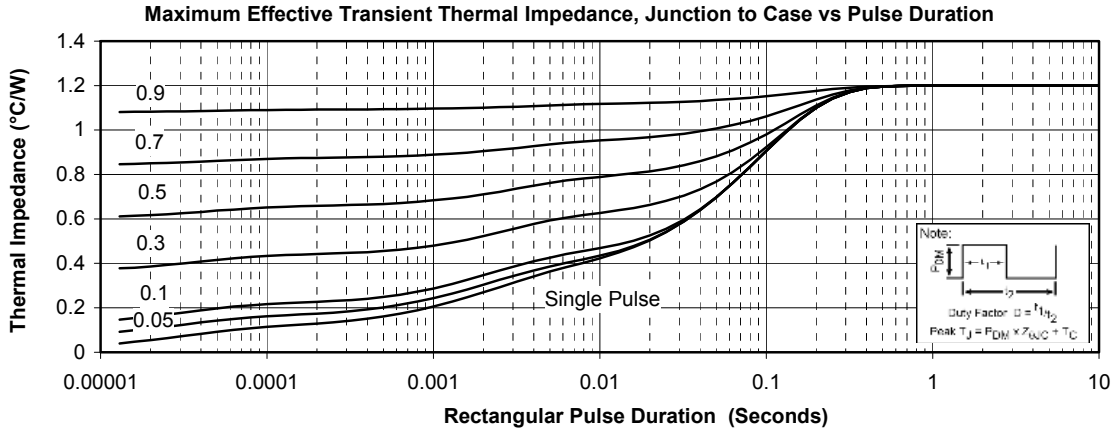


CR7 & CR8 Typical performance curve









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